

1. General description

AC Thyristor Triac power switch in a SOT428 (DPAK) surface mountable plastic package with self-protective clamping capabilities against low and high energy transients.

2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- Direct interfacing with low power drivers and microcontrollers
- Full cycle AC conduction
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Protective self turn-on capability for high energy transients
- Safe clamping capability for low energy over-voltage transients
- Sensitive gate for easy logic level triggering
- Surface mountable package
- Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt

3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Reversing induction motor controls

4. Quick reference data

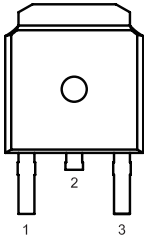

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 115\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	2	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	-	15.4	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	14	A
T_j	junction temperature		-	-	125	°C
V_{PP}	peak pulse voltage	$T_j = 25\text{ °C}$; non-repetitive, off-state; Fig. 6	-	-	2	kV

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I _{GT}	gate trigger current	V _D = 12 V; I _T = 100 mA; LD+ G+; T _j = 25 °C; Fig. 8	-	-	10	mA
		V _D = 12 V; I _T = 100 mA; LD+ G-; T _j = 25 °C; Fig. 8	-	-	10	mA
		V _D = 12 V; I _T = 100 mA; LD- G-; T _j = 25 °C; Fig. 8	-	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; Fig. 10	-	-	25	mA
V _T	on-state voltage	I _T = 3 A; T _j = 25 °C; Fig. 11	-	-	2	V
V _{CL}	clamping voltage	I _{CL} = 0.1 mA; t _p = 1 ms; T _j = 25 °C	850	-	-	V
Dynamic characteristics						
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 536 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit; Fig. 13	500	-	-	V/μs
di _{com} /dt	rate of change of commutating current	V _D = 400 V; T _j = 125 °C; I _{T(RMS)} = 2 A; dV _{com} /dt = 10 V/μs; gate open circuit; Fig. 14 ; Fig. 15	3	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		 sym037
2	A	anode		
3	G	gate		
mb	A	mounting base; connected to anode		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
ACTT2S-800E	TO252	ACTT2S-800E,118	Reel	2500	TO252N	07-Mar-2025
					TO252Q	05-Mar-2025

Type number	Marking codes	
	Assembly factory: N	Assembly factory: Q
ACTT2S-800E	ACTT2S 800E PJNxxxx xx	ACTT2S 800E PJQxxxx xx

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 115\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	2	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	15.4	A
		full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	14	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine-wave pulse	-	0.98	A ² s
di_T/dt	rate of rise of on-state current	$I_G = 20\text{ mA}$	-	100	A/ μ s
I_{GM}	peak gate current	$t = 20\text{ }\mu$ s	-	2	A
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T_j	junction temperature		-	125	°C
V_{PP}	peak pulse voltage	$T_j = 25\text{ °C}$; non-repetitive, off-state; Fig. 6	-	2	kV

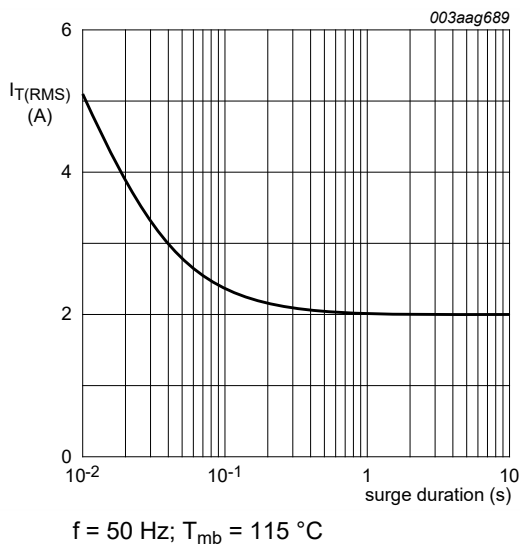


Fig. 1. RMS on-state current as a function of surge duration; maximum values

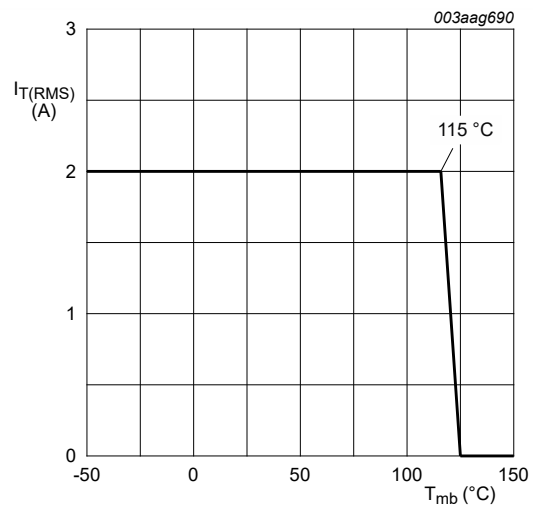


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

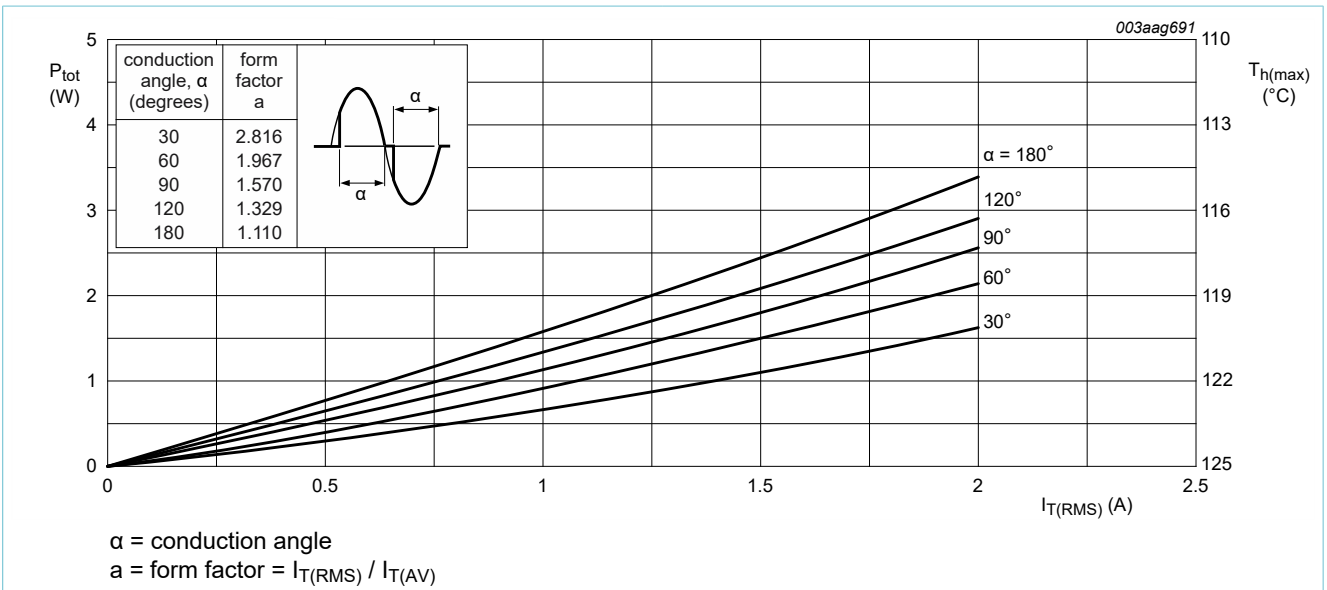


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

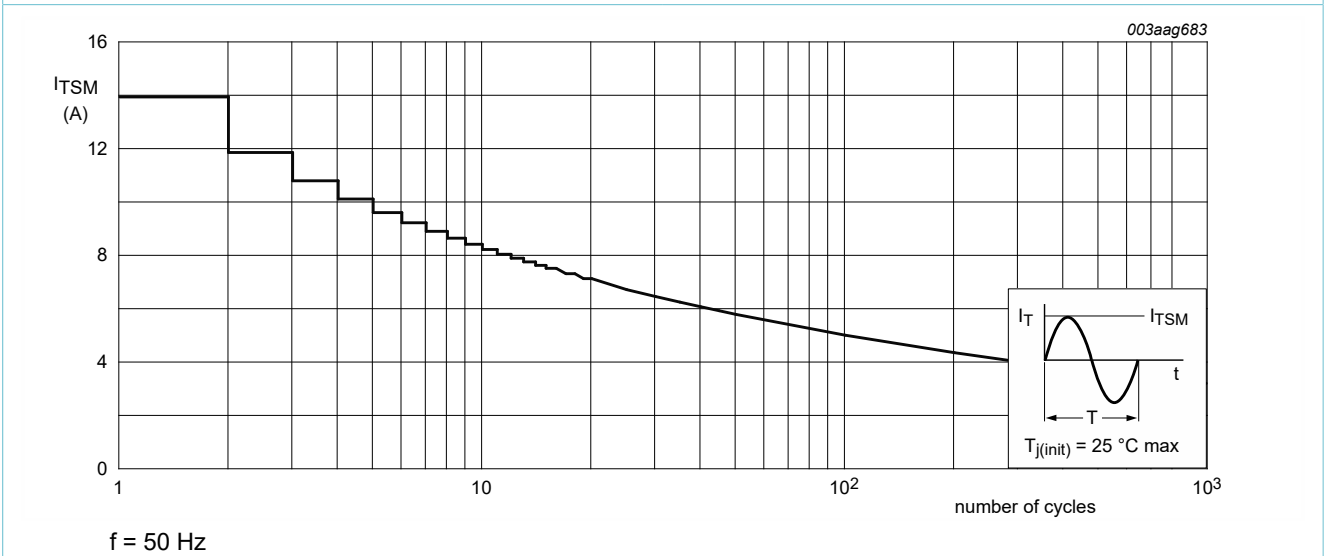


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

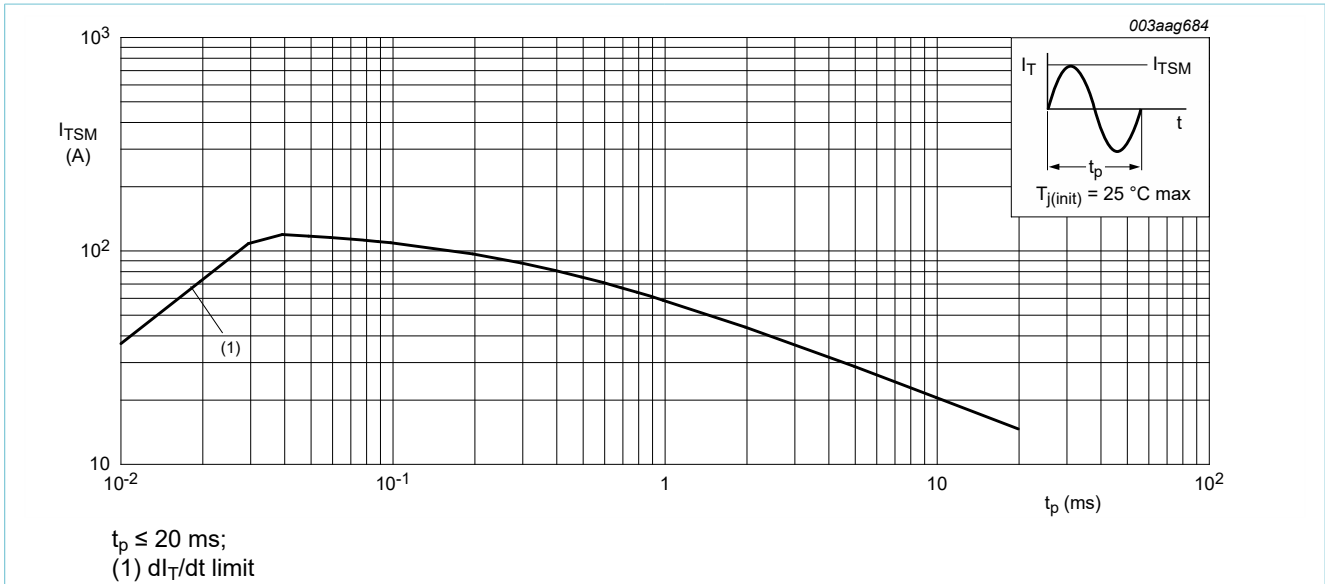


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

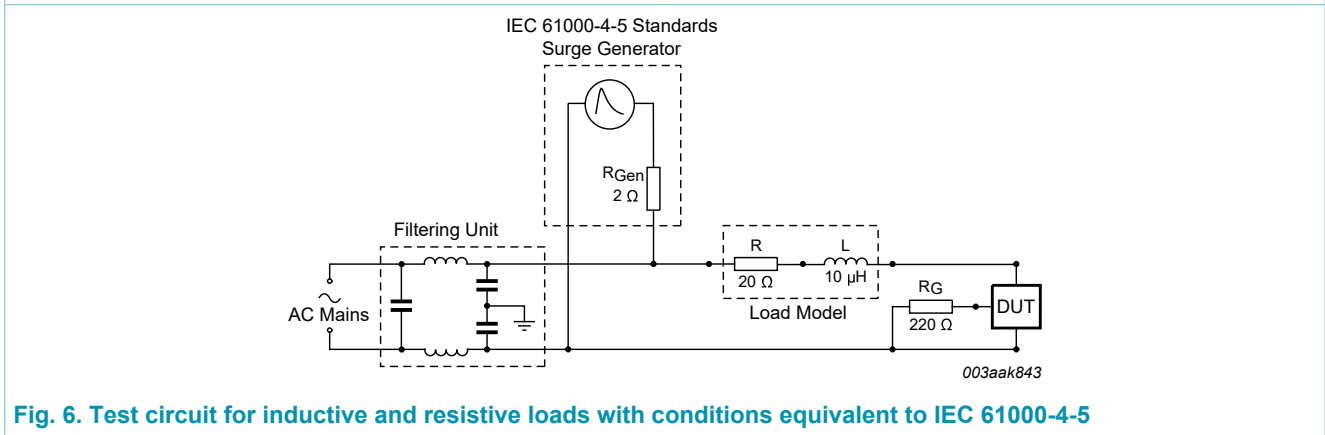
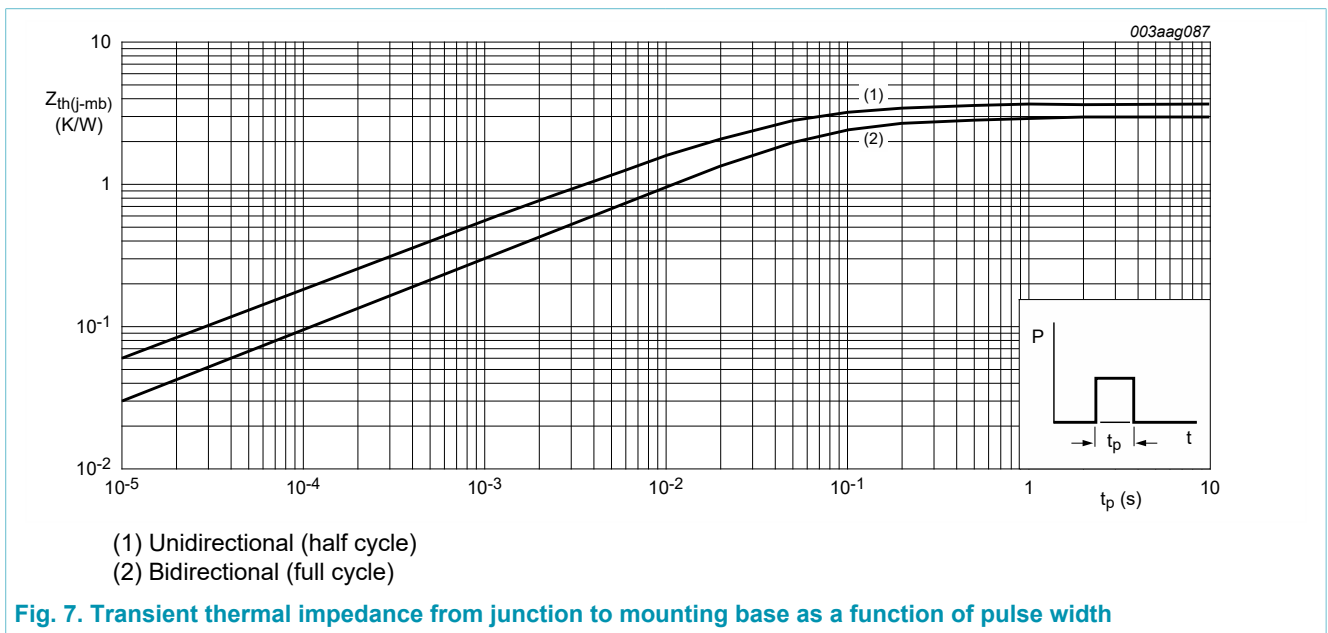


Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; Fig. 7	-	-	3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted	-	75	-	K/W



9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I _{GT}	gate trigger current	V _D = 12 V; I _T = 100 mA; LD+ G+; T _j = 25 °C; Fig. 8	-	-	10	mA
		V _D = 12 V; I _T = 100 mA; LD+ G-; T _j = 25 °C; Fig. 8	-	-	10	mA
		V _D = 12 V; I _T = 100 mA; LD- G-; T _j = 25 °C; Fig. 8	-	-	10	mA
I _L	latching current	V _D = 12 V; I _G = 100 mA; LD+ G+; T _j = 25 °C; Fig. 9	-	-	25	mA
		V _D = 12 V; I _G = 100 mA; LD+ G-; T _j = 25 °C; Fig. 9	-	-	35	mA
		V _D = 12 V; I _G = 100 mA; LD- G-; T _j = 25 °C; Fig. 9	-	-	25	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; Fig. 10	-	-	25	mA
V _T	on-state voltage	I _T = 3 A; T _j = 25 °C; Fig. 11	-	-	2	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 100 mA; T _j = 25 °C; Fig. 12	-	0.8	1	V
		V _D = 400 V; I _T = 100 mA; T _j = 125 °C; Fig. 12	0.2	0.45	-	V
I _D	off-state current	V _D = 800 V; T _j = 25 °C	-	-	10	μA
		V _D = 800 V; T _j = 125 °C	-	-	0.5	mA
V _{CL}	clamping voltage	I _{CL} = 0.1 mA; t _p = 1 ms; T _j = 25 °C	850	-	-	V
Dynamic characteristics						
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 536 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit; Fig. 13	500	-	-	V/μs
di _{com} /dt	rate of change of commutating current	V _D = 400 V; T _j = 125 °C; I _{T(RMS)} = 2 A; dV _{com} /dt = 10 V/μs; gate open circuit; Fig. 14 ; Fig. 15	3	-	-	A/ms

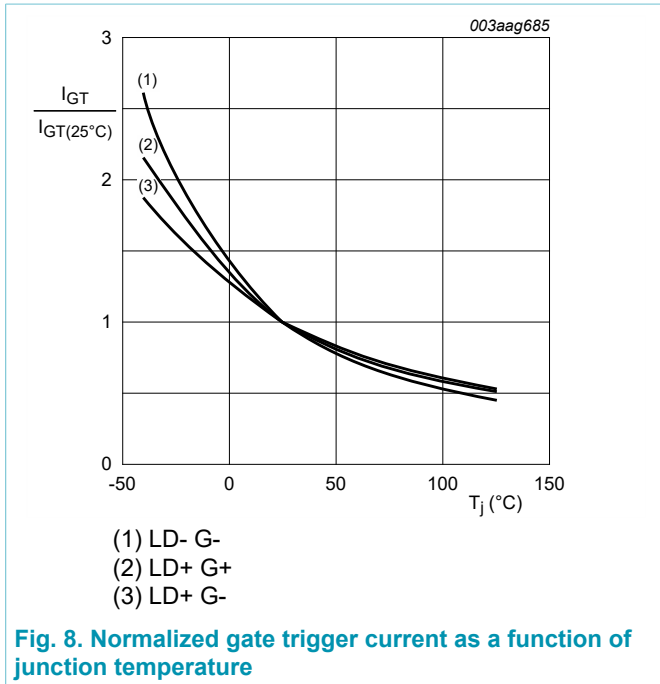


Fig. 8. Normalized gate trigger current as a function of junction temperature

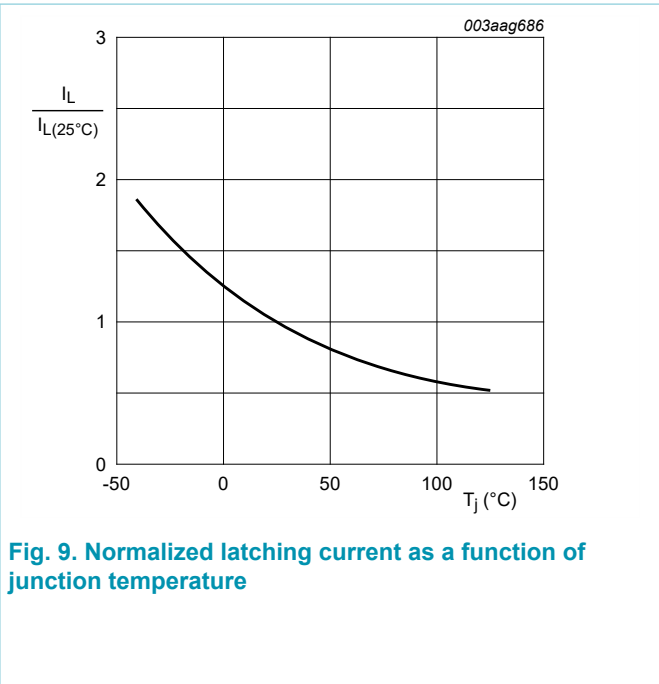


Fig. 9. Normalized latching current as a function of junction temperature

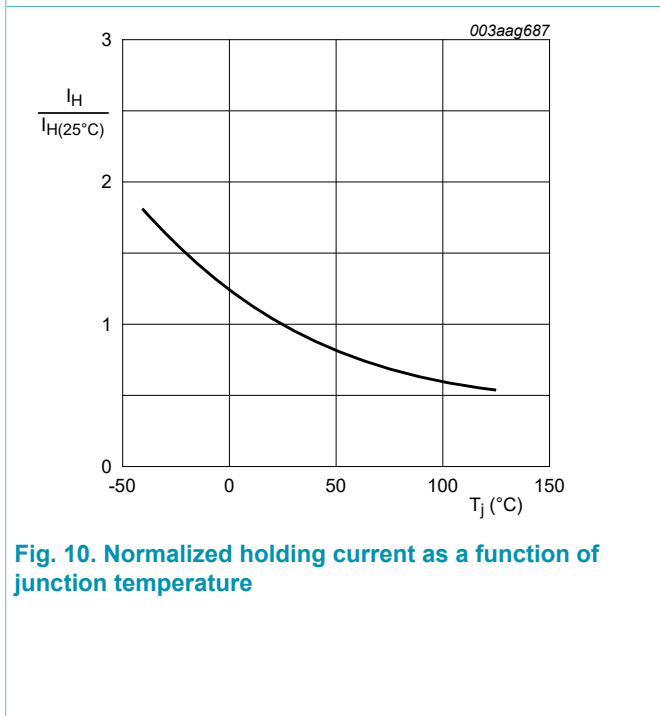


Fig. 10. Normalized holding current as a function of junction temperature

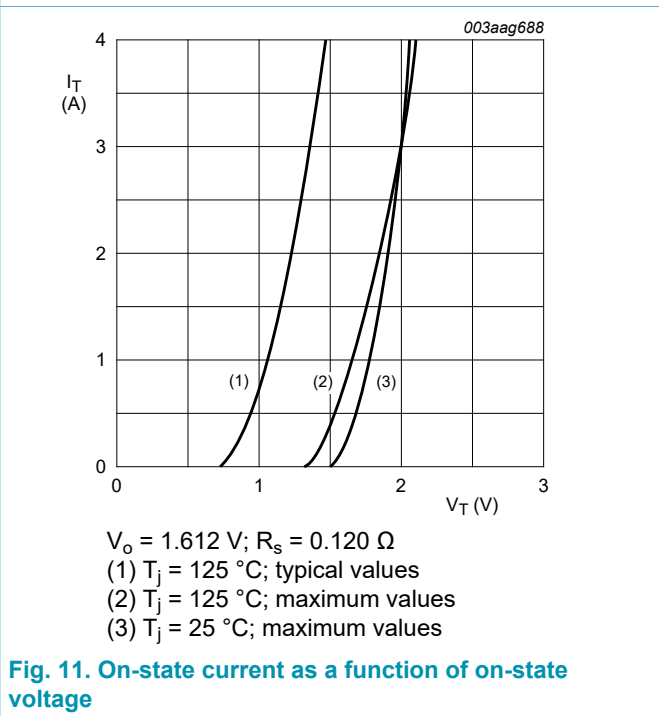


Fig. 11. On-state current as a function of on-state voltage

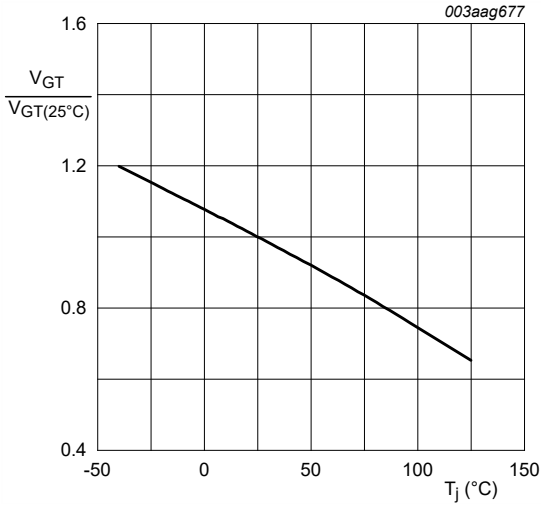
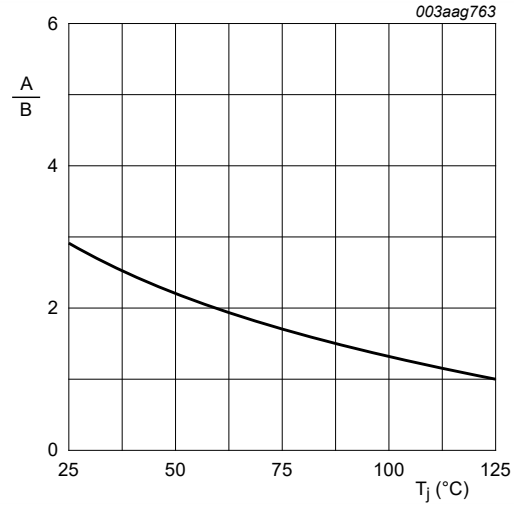
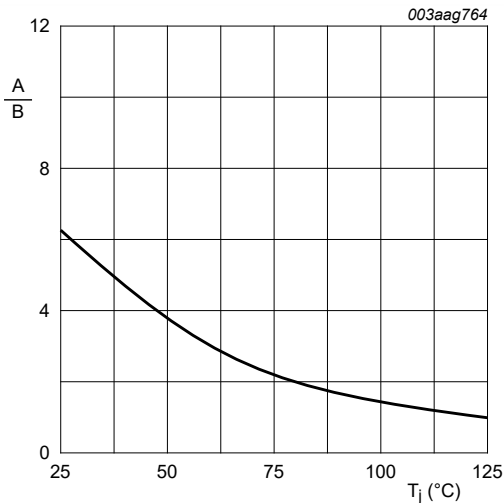


Fig. 12. Normalized gate trigger voltage as a function of junction temperature



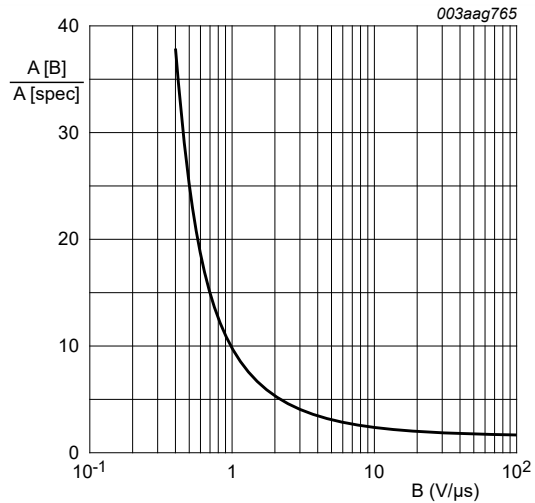
A = dV_D/dt at condition T_j °C
 B = dV_D/dt at condition T_j [125] °C

Fig. 13. Normalized rate of rise of off-state voltage as a function of junction temperature



A = di_{com}/dt at condition T_j °C
 B = di_{com}/dt at condition T_j [125] °C
 $V_D = 400$ V

Fig. 14. Normalized critical rate of rise of commutating current as a function of junction temperature



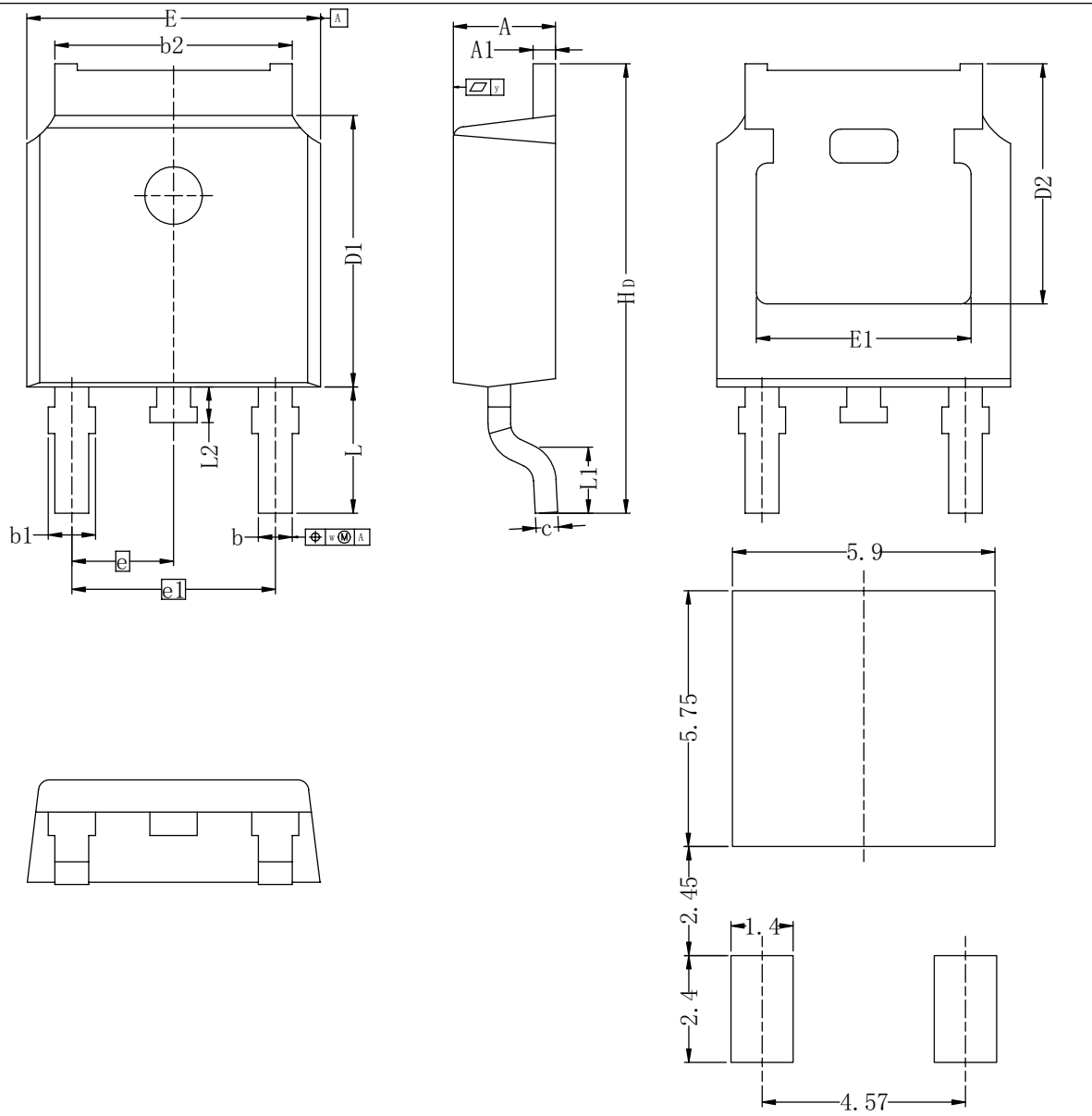
A [B] = di_{com}/dt at condition B, dV_{com}/dt
 A [spec] is the data sheet value for di_{com}/dt
 turn-off time is less than 20 ms

Fig. 15. Normalized critical rate of change of commutating current as a function of critical rate of change of commutating voltage; minimum values

10. Package outline

Assembly factory: N

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)



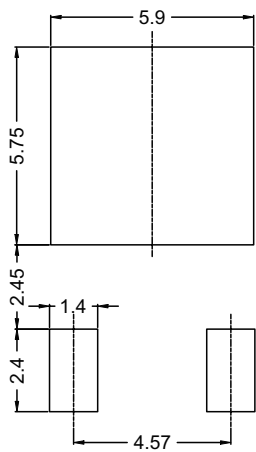
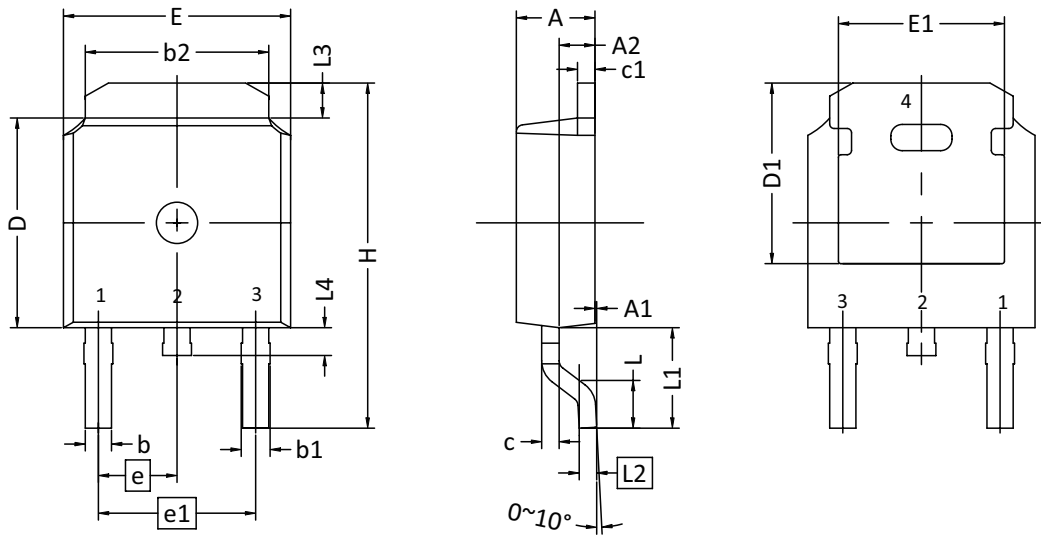
Recommended Footprint

Unit	A	A1	b	b1	b2	c	D1	D2	E	E1	e	e1	H _D	L	L1	L2	w	y
min	2.22	0.46	0.71	0.72	5.00	0.20	5.98	4.00	6.47	4.45	2.285	4.57	9.60	2.90	0.50	0.50	0.20	0.20
nom														2.90				
max	2.38	0.93	0.89	1.10	5.46	0.56	6.22	---	6.73	---			10.40	---	0.90			

Assembly factory: Q

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

TO252



Recommended Footprint

SYMBOLS	DIMENSION IN MM		
	MIN	NOM	MAX
A	2.184	2.286	2.400
A1	0.000	---	0.200
A2	0.889	1.041	1.170
b	0.635	0.762	0.889
b1	0.680	0.840	1.143
b2	4.953	5.340	5.500
c	0.450	0.508	0.610
c1	0.450	0.508	0.630
D	5.969	6.096	6.223
D1	5.210	5.249	5.380
E	6.350	6.604	6.800
E1	4.318	4.826	4.920
e	2.286BSC		
e1	4.572BSC		
H	9.398	10.033	10.500
L	1.270	1.520	2.032
L1	2.921REF		
L2	0.408	0.508	0.608
L3	0.889	1.016	1.270
L4	0.600	---	1.016

11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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